



### 50V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage

50 V

Current

360mA

#### **Features**

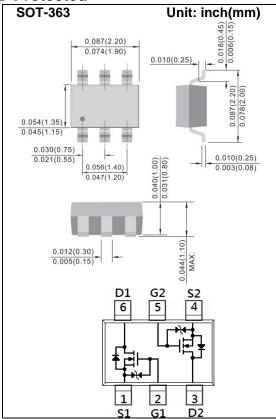
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V, I<sub>D</sub>@500mA<1.6Ω</li>
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@200mA<2.5Ω</li>
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@2.5V, I<sub>D</sub>@100mA<4.5Ω</li>
- Advanced Trench Process Technology
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc
- ESD Protected 2KV HBM
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: SOT-363 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0002 ounces, 0.006 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	50	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20		
Continuous Drain Current (Note 4)		I <sub>D</sub>	360	mA	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	1200		
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	236	mW	
	Derate above 25°C		1.89	mW/°C	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient (Note 3,4)		$R_{ heta JA}$	530	°C/W	





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{DSS}$ $V_{GS}=0V$ , $I_{D}=250uA$	50	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.8	1	1.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA	-	0.96	1.6	Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	1.25	2.5	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =100mA	-	2.73	4.5	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =25V, I <sub>D</sub> =250mA, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.63	1	nC
Gate-Source Charge	$Q_gs$		-	0.2	-	
Gate-Drain Charge	$Q_gd$		-	0.23	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHZ	-	25	50	pF
Output Capacitance	Coss		-	9.5	20	
Reverse Transfer Capacitance	Crss		-	2.1	5	
Turn-On Delay Time	td <sub>(on)</sub>	\\	-	2.2	5	ns
Turn-On Rise Time	tr	$V_{DD}$ =25V, $I_{D}$ =500mA, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 1.2)	-	19.2	38	
Turn-Off Delay Time	td <sub>(off)</sub>		-	6.2	12	
Turn-Off Fall Time	tf	K <sub>G</sub> =012	-	23	50	
Drain-Source Diode						
Maximum Continuous Drain-Source					500	mA
Diode Forward Current	I <sub>S</sub>		_	_	500	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V	-	0.86	1.5	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

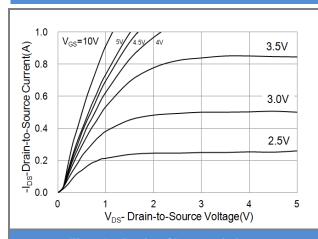
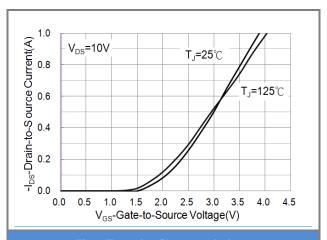


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

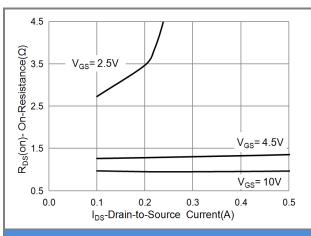


Fig.3 On-Resistance vs. Drain Current

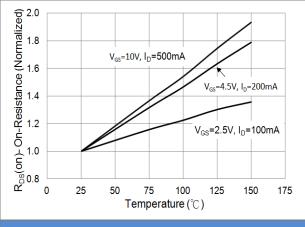


Fig.4 On-Resistance vs. Junction temperature

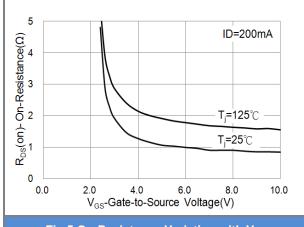
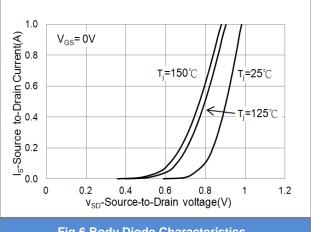


Fig.5 On-Resistance Variation with V<sub>GS</sub>



**Fig.6 Body Diode Characteristics** 





#### **TYPICAL CHARACTERISTIC CURVES**

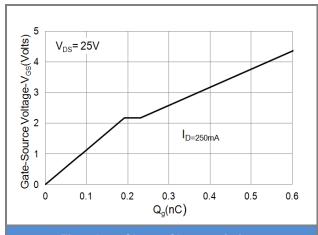


Fig.7 Gate-Charge Characteristics

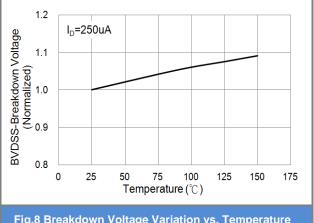


Fig.8 Breakdown Voltage Variation vs. Temperature

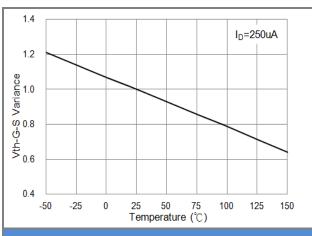


Fig.9 Threshold Voltage Variation with Temperature

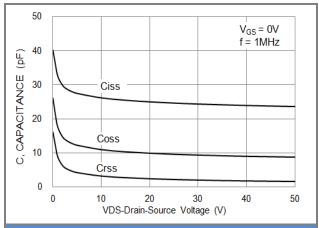


Fig.10 Capacitance vs. Drain-Source Voltage

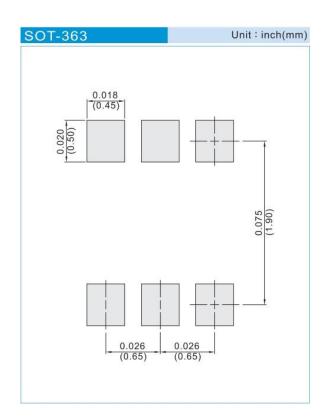




### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJT138K-AU_R1_000A1	SOT-363	3K pcs / 7" reel	8KD	Halogen free

### **Mounting Pad Layout**







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